# MTM13127

## Silicon P-channel MOS FET

For DC-DC converter circuits For swiching circuits

#### Overview

MTM13127 is the P-channel MOS FET that is highly suitable of DC-DC converter and other switching circuits.

#### ■ Features

- Low drain-source ON resistance:  $R_{DS(on)}$  typ. = 161 m $\Omega$  ( $V_{GS}$  = -1.8 V)
- Low drive voltage: 1.8 V
- Contributes to miniaturization of sets, mount area reduction
- Eco-friendly Halogen-free package

#### Packaging

MTM131270BBF Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Drain-source surrender voltage	V <sub>DSS</sub>	-20	V	
Gate-source surrender voltage	V <sub>GSS</sub>	±10	V	
Drain current	$I_D$	-2.0	A	
Peak drain current	$I_{DP}$	-8.0	A	
Power dissipation *	$P_{\mathrm{D}}$	700	mW	
Channel temperature	T <sub>ch</sub>	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	

Note) \*1: Pulse width  $\leq 10 \mu s$ , Duty Cycle  $\leq 1\%$ 

#### ■ Package

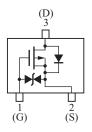
Code

Mini3-G3-B

Package dimension clicks here.→

- Pin Name
  - 1: Gate
  - 2: Source
  - 3: Drain
- Marking Symbol: EU

### ■ Internal Connection



<sup>\*2:</sup> Measuring on ceramic substrate at 40 mm  $\times$  38 mm  $\times$  0.2 mm  $P_D$  absolute maximum rating without a heat shink: 150 mW

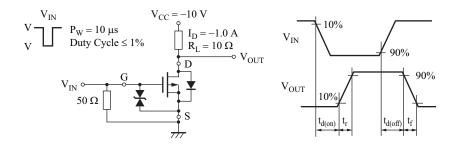
MTM13127 Panasonic

# ■ Electrical Characteristics $T_a = 25$ °C±3°C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source surrender voltage	V <sub>DSS</sub>	$I_D = -1.0 \text{ mA}, V_{GS} = 0$	-20			V
Drain-source cutoff current	$I_{DSS}$	$V_{DS} = -20 \text{ V}, V_{GS} = 0$			-1.0	μΑ
Gate-source cutoff current	I <sub>GSS</sub>	$V_{GS} = \pm 8 \text{ V}, V_{DS} = 0$			±10	μΑ
Gate threshold voltage	$V_{TH}$	$I_D = -1.0 \text{ mA}, V_{DS} = -10 \text{ V}$	- 0.4	- 0.75	-1.10	V
Drain-source ON resistance 1 *1	R <sub>DS(on)</sub> 1	$I_D = -1.0 \text{ A}, V_{GS} = -4.0 \text{ V}$		92	130	mΩ
Drain-source ON resistance 2 *1	R <sub>DS(on)</sub> 2	$I_D = -1.0 \text{ A}, V_{GS} = -2.5 \text{ V}$		115	210	mΩ
Drain-source ON resistance 3 *1	R <sub>DS(on)</sub> 3	$I_D = -0.5 \text{ A}, V_{GS} = -1.8 \text{ V}$		161	280	mΩ
Forward transfer admittance *1	Y <sub>fs</sub>	$I_D = -1.0 \text{ A}, V_{DS} = -10 \text{ V}, f = 1 \text{ kHz}$	3.0			S
Short-circuit input capacitance (Common source)	C <sub>iss</sub>			300		pF
Short-circuit output capacitance (Common source)	Coss	$V_{DS} = -10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		30		pF
Reverse transfer capacitance (Common source)	C <sub>rss</sub>			35		pF
Turn-on delay time *2	t <sub>d(on)</sub>	V 10 V V 0 V 4 V V 10 4		6		ns
Rise time *2	t <sub>r</sub>	$V_{DD} = -10 \text{ V}, V_{GS} = 0 \text{ V to } -4 \text{ V}, I_D = -1.0 \text{ A}$		8		ns
Turn-off delay time *2	t <sub>d(off)</sub>	V 10 V V 4 V 4 OV I 1 O A		57		ns
Fall time *2	$t_{\mathrm{f}}$	$V_{DD} = -10 \text{ V}, V_{GS} = -4 \text{ V to } 0 \text{ V}, I_D = -1.0 \text{ A}$		55		ns

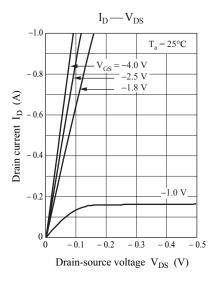
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

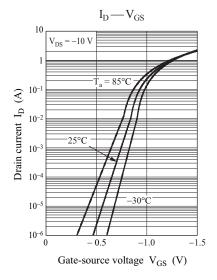
- 2. \*1: Pulse measurement
  - \*2: Test circuit

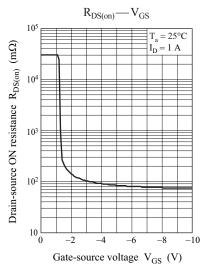


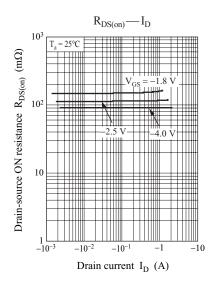
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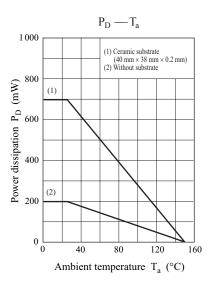
Panasonic MTM13127

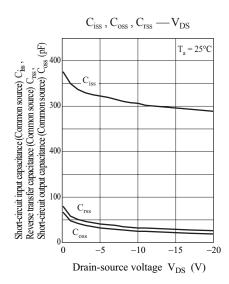












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